

Title (en)

SEMICONDUCTOR STRUCTURE AND ETCH TECHNIQUE FOR MONOLITHIC INTEGRATION OF III-N TRANSISTORS

Title (de)

HALBLEITERSTRUKTUR UND ÄTZTECHNIK ZUR MONOLITHISCHEN INTEGRATION VON III-N-TRANSISTOREN

Title (fr)

STRUCTURE SEMI-CONDUCTRICE ET TECHNIQUE DE GRAVURE POUR L'INTÉGRATION MONOLITHIQUE DE TRANSISTORS AU N-III

Publication

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Application

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CPC (source: EP US)

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Citation (search report)

- [I] WO 2014078699 A1 20140522 - MASSACHUSETTS INST TECHNOLOGY [US]
- [A] KONG YUECHAN ET AL: "Monolithic Integration of E/D-Mode AlGaIn/GaN MIS-HEMTs", IEEE ELECTRON DEVICE LETTERS, IEEE SERVICE CENTER, NEW YORK, NY, US, vol. 35, no. 3, March 2014 (2014-03-01), pages 336 - 338, XP011540617, ISSN: 0741-3106, [retrieved on 20140220], DOI: 10.1109/LED.2013.2297433
- See references of WO 2017176612A1

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